

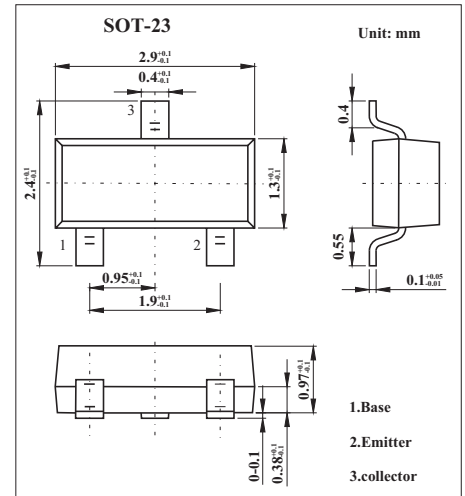
SOT-23 Plastic-Encapsulate Transistors

Features

- Low $V_{CE(sat)}, V_{CE(sat)} \leq -0.5V$ ($I_C / I_B = -0.5A / -50mA$) .
- $I_C = -0.8A$.
- PNP silicon transistor

MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

| Parameter | Symbol | Rating | Unit |
|-----------------------------|-----------|-------------|------|
| Collector-base Voltage | V_{CBO} | -40 | V |
| Collector-emitter Voltage | V_{CEO} | -32 | V |
| Emitter-base Voltage | V_{EBO} | -5 | V |
| Collector current | I_C | -0.8 | A |
| Collector power dissipation | P_C | 0.2 | W |
| Jumction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -55 to +150 | °C |

PACKAGE INFORMATION

| Device | Package | Shipping |
|---------|---------|----------------|
| 2SB1197 | SOT-23 | 3000/Tape&Reel |

| Parameter | Symbol | Testconditons | Min | Typ | Max | Unit |
|--------------------------------------|---------------|--|-----|-----|------|---------|
| Collector-base breakdown voltae | V_{CBO} | $I_C = -50 \mu A$ | -40 | | | V |
| Collector-emitter breakdown voltage | V_{CEO} | $I_C = -1mA$ | -32 | | | V |
| Emitter-base breakdown voltage | V_{EBO} | $I_E = -50 \mu A$ | -5 | | | V |
| Collector cutoff current | I_{CBO} | $V_{CB} = -20V$ | | | -0.5 | μA |
| Emitter cutoff current | I_{EBO} | $V_{EB} = -4V$ | | | -0.5 | μA |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = -0.5A, I_B = -50mA$ | | | -0.5 | V |
| DC current transfer ratio | h_{FE} | $V_{CE} = -3V, I_C = -100mA$ | 120 | | 390 | |
| Output Capacitance | C_{ob} | $V_{CB} = -10V, I_E = 0A, f = 1MHz$ | | 12 | 30 | pF |
| Transition frequency | f_T | $V_{CE} = -5V, I_E = 50mA, f = 100MHz$ | | 200 | | MHz |

hFE Classification

| Marking | AHQ | AHR |
|---------|---------|---------|
| Rank | Q | R |
| hFE | 120~270 | 180~390 |